

Description

The MMFTP3334K-AQ uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V.

This device is suitable for use as a Battery protection or in other Switching application.

D S S

SOT-23

General Features

 $V_{DS} = -30V, I_{D} = -4.1A$

 $R_{DS(ON)}$ <56m Ω @ V_{GS} =10V

Application

Power management

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MMFTP3334K-AQ	SOT-23	3407 XXXX	3000PCS

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	-30	V
V _G s	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	-4.1	А
Ірм	Drain Current-Pulsed (Note 1)	-13	А
P _D	Maximum Power Dissipation	1.32	W
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	125	°C/W



Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			V	
△BV _{DSS} /△T _J	BVDSS Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.02		V/°C	
R _{DS(ON)}	Static Drain Source On Begintance?	V _{GS} =-10V , I _D =-3A		48	56	mO	
	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V , I _D =-1.5A	A 78 90		90	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage	V -V I - 250::A	-1.2	-1.5	-2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=-250uA$		4.32		mV/°C	
	Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =25°C			-1	uA	
IDSS		V _{DS} =-24V , V _{GS} =0V , T _J =55°C			-5		
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA	
gfs	Forward Transconductance	V_{DS} =-5V , I_{D} =-3A		4.8		S	
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		24	48	Ω	
Qg	Total Gate Charge (-4.5V)			5.22	7.3		
Q _{gs}	Gate-Source Charge	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-3A		1.25	1.8	nC	
Q _{gd}	Gate-Drain Charge			2.3	3.2		
T _{d(on)}	Turn-On Delay Time			18.4	37		
Tr	Rise Time	V_{DD} =-15V , V_{GS} =-10V , R_{G} =3.3 Ω		11.4	21	ns	
T _{d(off)}	Turn-Off Delay Time	I _D =-1A		39.4	79		
T _f	Fall Time			5.2	10.4		
Ciss	Input Capacitance			463	650		
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		82	115	pF	
C _{rss}	Reverse Transfer Capacitance			68	95		
Is	Continuous Source Current ^{1,4}	VV0V Force Current			-3.2	Α	
I _{SM}	Pulsed Source Current ^{2,4}	──V _G =V _D =0V , Force Current			-13	Α	
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1	V	

^{1.} The data tested by surface mounted on a 1 inch $^2\,\text{FR-4}$ board with 2OZ copper.

^{2.}The data tested by pulsed , pulse width $\leq 300 us$, duty cycle $\leq 2\%$ 3.The power dissipation is limited by 150°C junction temperature

^{4.} The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

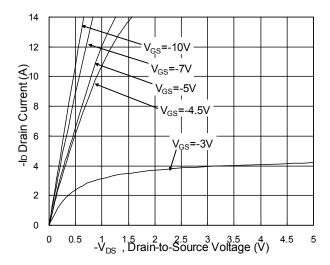


Fig.1 Typical Output Characteristics

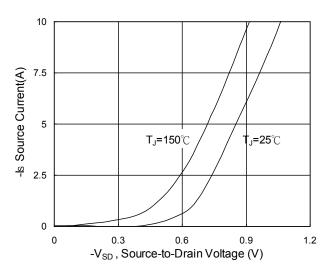


Fig.3 Source Drain Forward Characteristics

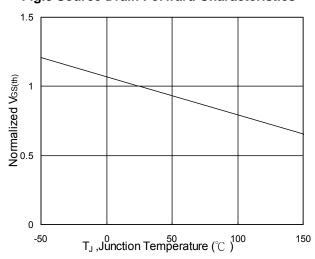


Fig.5 Normalized V_{GS(th)} vs. T_J

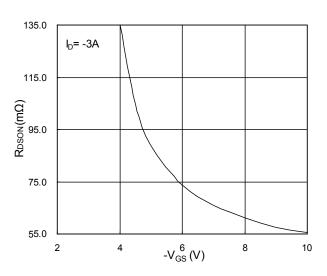


Fig.2 On-Resistance vs. G-S Voltage

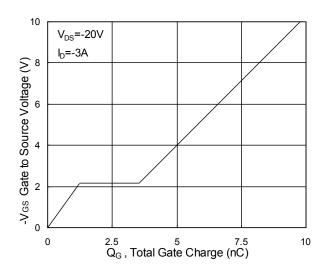


Fig.4 Gate-Charge Characteristics

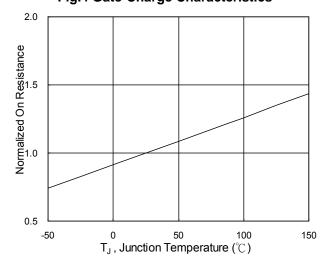
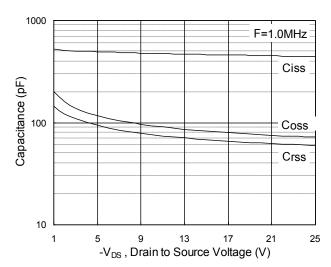


Fig.6 Normalized R_{DSON} vs. T_J



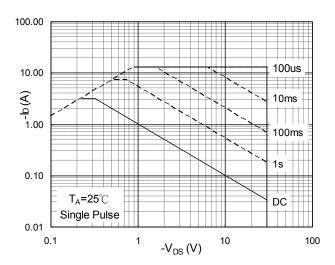


Fig.7 Capacitance

Fig.8 Safe Operating Area

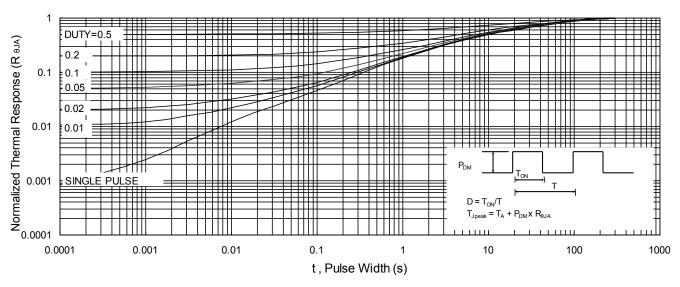
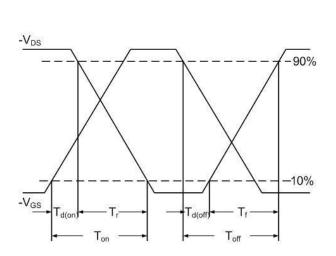


Fig.9 Normalized Maximum Transient Thermal Impedance



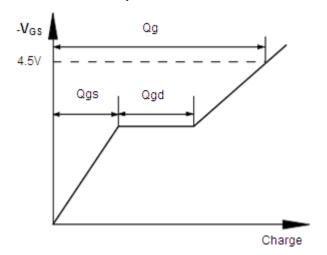
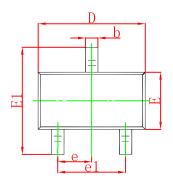


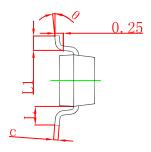
Fig.10 Switching Time Waveform

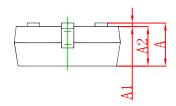
Fig.11 Gate Charge Waveform



SOT-23 Package Outline Dimensions

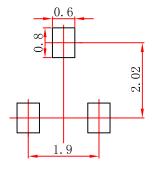






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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